

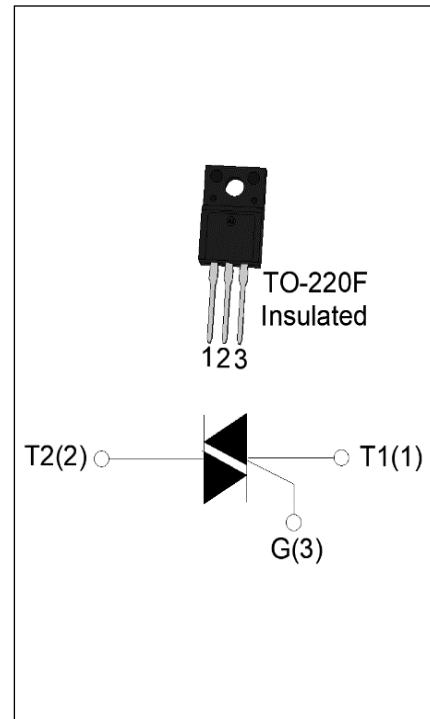


## JST08F-800C 8A TRIAC

Rev.A.1.0

**DESCRIPTION:**

The JST08F-800C triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an external plastic package, JST08F-800C provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT\text{ I/II/III/IV}}$	25/25/25/50	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c \leqslant 93^\circ\text{C}$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		88	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	32	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	I - II III-IV	80 40	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W

Peak pulse voltage (T <sub>j</sub> =25°C; non-repetitive,off-state;FIG.7)	V <sub>PP</sub>	1	kV
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**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**

Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II - III	MAX.	25	mA
		IV		50	
V <sub>GT</sub>		ALL	MAX.	1	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	ALL	MIN.	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III - IV	MAX.	40	mA
		II		80	
I <sub>H</sub>	I <sub>T</sub> =200mA		MAX.	30	mA
dV/dt	V <sub>D</sub> =540V Gate Open T <sub>j</sub> =125°C		MIN.	500	V/μs
(dV/dt)c	(dI/dt)c=3.5A/ms, T <sub>j</sub> =125°C		MIN.	6	V/μs
t <sub>on</sub>	I <sub>G</sub> =80mA I <sub>A</sub> =400mA I <sub>R</sub> =40mA T <sub>j</sub> =25°C		TYP.	5	μs
t <sub>off</sub>				30	

**STATIC CHARACTERISTICS**

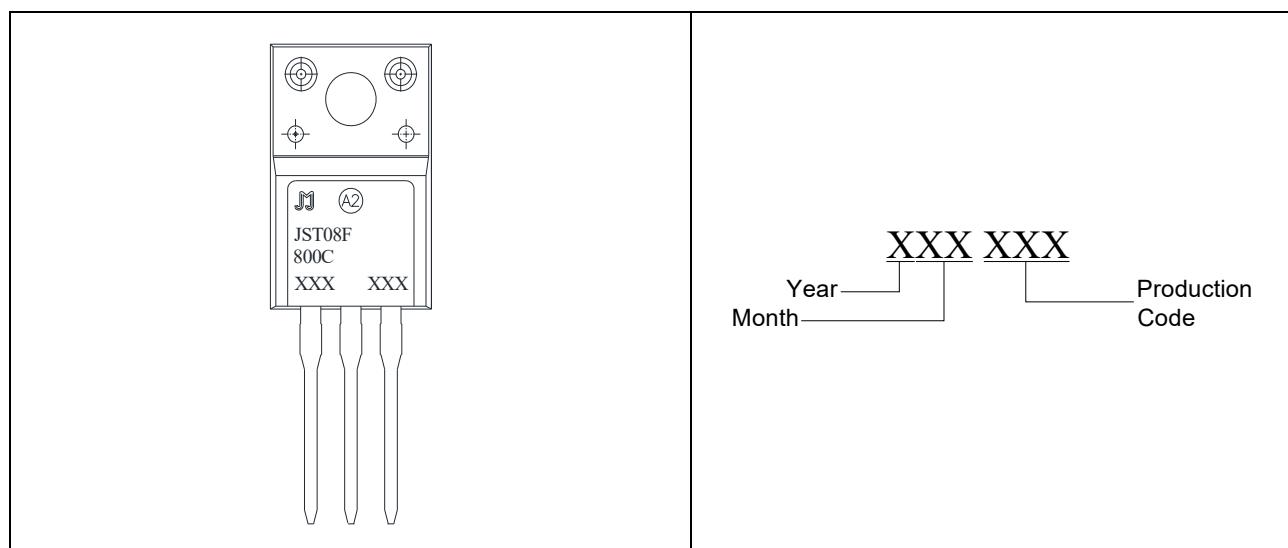
Symbol	Parameter		Value(MAX.)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =11A t <sub>p</sub> =380μs	T <sub>j</sub> =25°C	1.5	V
V <sub>TO</sub>	Threshold voltage	T <sub>j</sub> =125°C	0.81	V
R <sub>D</sub>	Dynamic resistance	T <sub>j</sub> =125°C	44	mΩ
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	5	μA
I <sub>RRM</sub>		T <sub>j</sub> =125°C	0.35	mA

**THERMAL RESISTANCES**

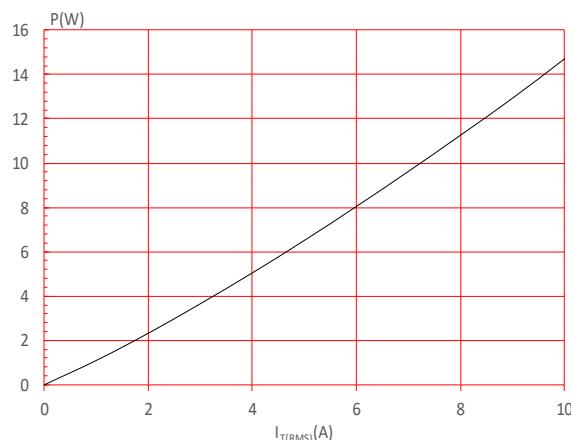
Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	junction to case (AC)	2.8	°C/W
R <sub>th(j-a)</sub>	junction to ambient (AC)	60	°C/W

**ORDERING INFORMATION**

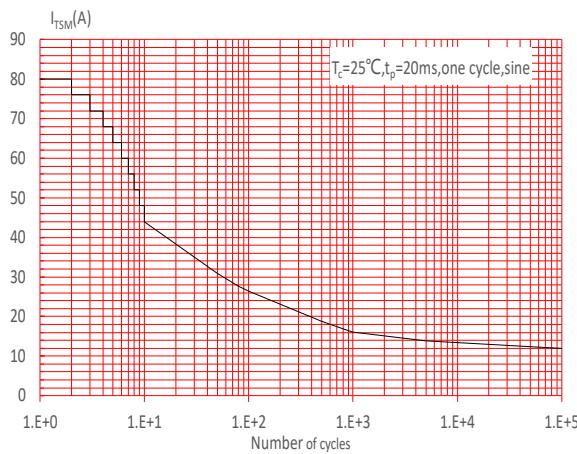
<b>J</b>	<b>ST</b>	<b>08</b>	<b>F</b>	<b>-800</b>	<b>C</b>
JieJie Microelectronics Co., Ltd					
	Triacs				
		<u>I<sub>T(RMS)</sub>:8A</u>			
			<u>F:TO-220F(Ins)</u>		
				800:V <sub>DRM</sub> / V <sub>RRM</sub> ≥ 800V	
					C: I <sub>GT1-3</sub> ≤ 25mA I <sub>GT4</sub> ≤ 50mA

**MARKING**

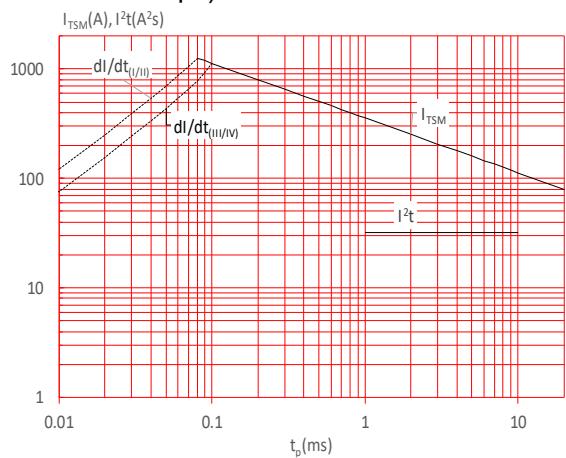
**FIG.1** Maximum power dissipation versus RMS on-state current



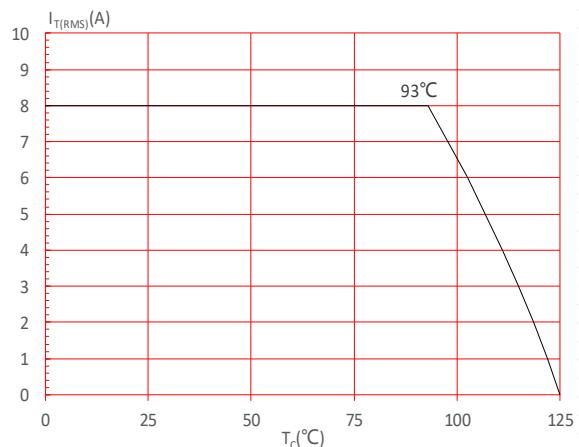
**FIG.3:** Surge peak on-state current versus number of cycles



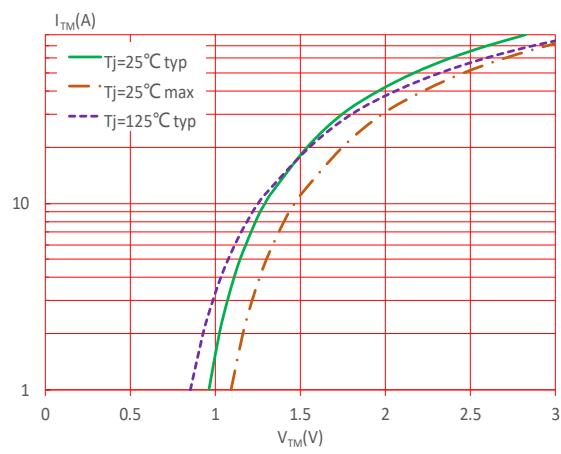
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( I - II :  $\text{d}I/\text{d}t < 80\text{A}/\mu\text{s}$ ; III-IV:  $\text{d}I/\text{d}t < 40\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

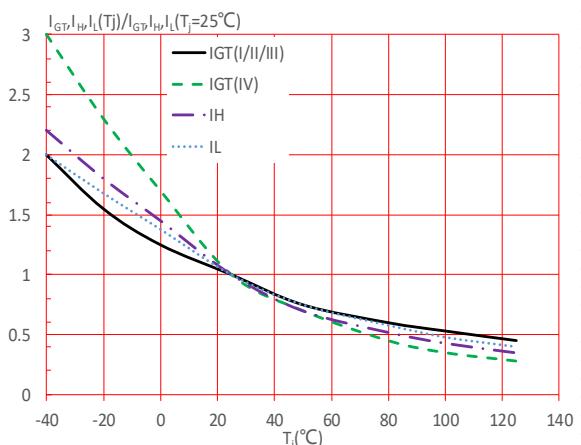
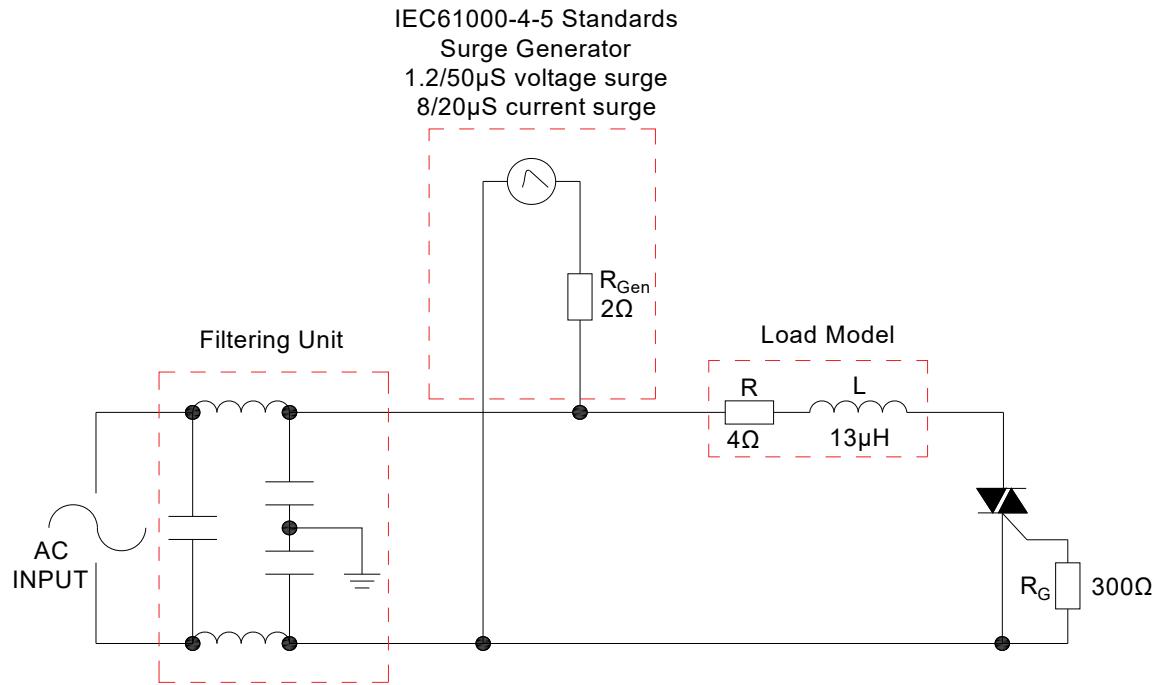


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

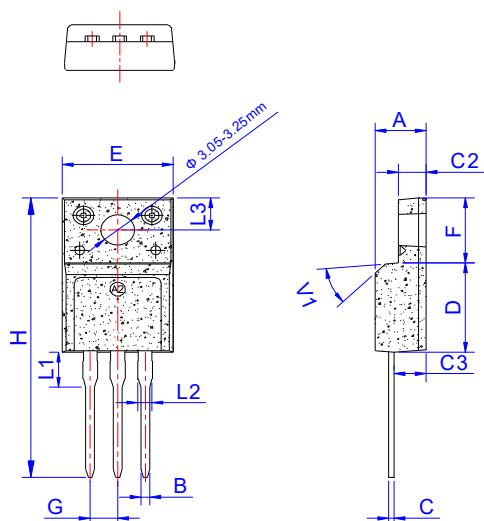
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II -III	IV			
<b>JST08F-800C</b>	<b>800</b>	<b>25</b>	<b>50</b>	<b>TO-220F(Ins)</b>	<b>50</b>	<b>Tube</b>

**Document Revision History**

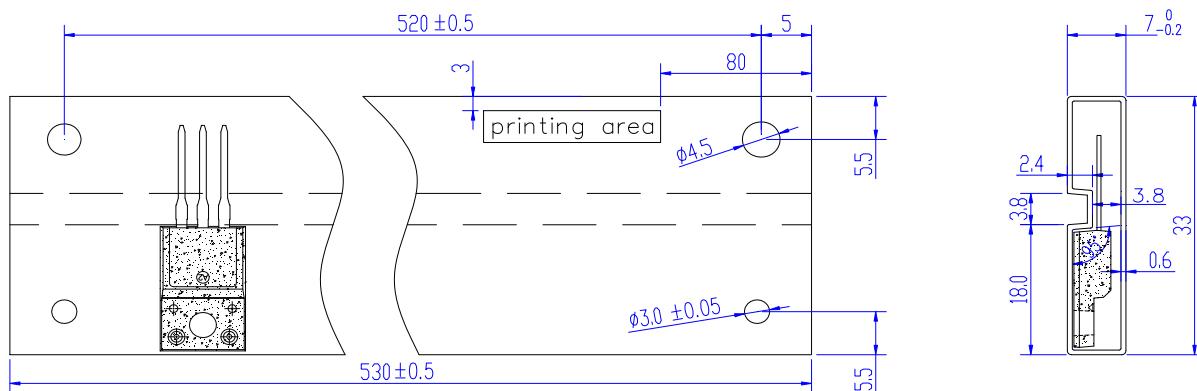
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1		45°			45°	

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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